

	Type	Hits	Search Text	DBs
1	BRS	964	372/102	USPAT; EPO; JPO; DERWENT; IBM_TDB
2	BRS	134080 1	substrate	USPAT; EPO; JPO; DERWENT; IBM_TDB
3	BRS	109128 1	semiconductor	USPAT; EPO; JPO; DERWENT; IBM_TDB
4	BRS	119623 2	insulat\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB
5	BRS	105588 6	reflect\$3 or mirror	USPAT; EPO; JPO; DERWENT; IBM_TDB
6	BRS	130761	lenses	USPAT; EPO; JPO; DERWENT; IBM_TDB
7	BRS	20963	sapphire	USPAT; EPO; JPO; DERWENT; IBM_TDB
8	BRS	174	substrate and semiconductor and insulat\$3 and (reflect\$3 or mirror) and lenses and sapphire	USPAT; EPO; JPO; DERWENT; IBM_TDB
9	BRS	12896	VCSEL SEL	USPAT; EPO; JPO; DERWENT; IBM_TDB
10	BRS	105588 6	reflect\$3 or mirror	USPAT; EPO; JPO; DERWENT; IBM_TDB
11	BRS	111121	clad cladding	USPAT; EPO; JPO; DERWENT; IBM_TDB
12	BRS	69307	(current optical) near4 (block blocking restricting restriction confin\$5)	USPAT; EPO; JPO; DERWENT; IBM_TDB
13	BRS	152	(VCSEL SEL) and (reflect\$3 or mirror) and (clad cladding) and ((current optical) near4 (block blocking restricting restriction confin\$5))	USPAT; EPO; JPO; DERWENT; IBM_TDB
14	BRS	9	("4902644" "5256596" "5317587" "5328854" "5343487" "5412680" "5457328" "5478774" "5493577").PN.	USPAT
15	IS&R	3	((("6018541") or ("6411642") or ("6356674")).PN.	USPAT
16	IS&R	5	((("5625636") or ("5625637") or ("5633527") or ("5925898") or ("6124974")).PN.	USPAT
17	IS&R	612	(372/36).CCLS.	USPAT; EPO; JPO; DERWENT; IBM_TDB
18	BRS	1	"5484799".PN.	USPAT
19	BRS	7	quantum adj well adj intermixed	USPAT; EPO; JPO; DERWENT; IBM_TDB
20	BRS	452	passive adj waveguide	USPAT; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
21	BRS	7	qwi	USPAT; EPO; JPO; DERWENT; IBM_TDB
22	BRS	6	qwi not (quantum adj well adj intermixed)	USPAT; EPO; JPO; DERWENT; IBM_TDB
23	BRS	2276	heatsink (haet adj sink)	USPAT; EPO; JPO; DERWENT; IBM_TDB
24	BRS	4	(passive adj waveguide) and (heatsink (haet adj sink))	USPAT; EPO; JPO; DERWENT; IBM_TDB
25	BRS	6	(passive adj4 waveguide) and (heatsink (haet adj sink))	USPAT; EPO; JPO; DERWENT; IBM_TDB
26	BRS	113	waveguide and (heatsink (haet adj sink))	USPAT; EPO; JPO; DERWENT; IBM_TDB
27	BRS	114308 5	semiconductor	USPAT; EPO; JPO; DERWENT; IBM_TDB
28	BRS	565292	laser	USPAT; EPO; JPO; DERWENT; IBM_TDB
29	BRS	59788	gallium adj nitride (Ga?N? Ga?sub.\$)	USPAT; EPO; JPO; DERWENT; IBM_TDB
30	BRS	968834	multiple aj quantum adj well MQW	USPAT; EPO; JPO; DERWENT; IBM_TDB
31	BRS	151739	ridge	USPAT; EPO; JPO; DERWENT; IBM_TDB
32	BRS	816	semiconductor and laser and (gallium adj nitride (Ga?N? Ga?sub.\$)) and (multiple aj quantum adj well MQW) and ridge	USPAT; EPO; JPO; DERWENT; IBM_TDB
33	BRS	2849	self adj3 oscillating	USPAT; EPO; JPO; DERWENT; IBM_TDB
34	BRS	413100	(driving adj current) (current adj driver) driver diving	USPAT; EPO; JPO; DERWENT; IBM_TDB
35	BRS	2	(semiconductor and laser and (gallium adj nitride (Ga?N? Ga?sub.\$)) and (multiple aj quantum adj well MQW) and ridge) and (self adj3 oscillating)	USPAT; EPO; JPO; DERWENT; IBM_TDB
36	BRS	120	(semiconductor and laser and (gallium adj nitride (Ga?N? Ga?sub.\$)) and (multiple aj quantum adj well MQW) and ridge) and ((driving adj current) (current adj driver) driver diving)	USPAT; EPO; JPO; DERWENT; IBM_TDB